

Description

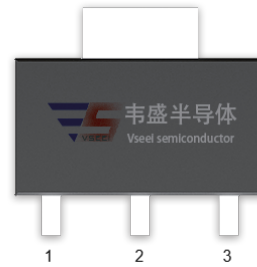
The VSM8N03 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

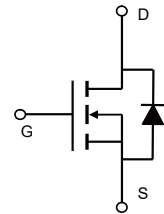
- $V_{DS} = 30V, I_D = 8A$
 $R_{DS(ON)} < 55m\Omega @ V_{GS}=2.5V$
 $R_{DS(ON)} < 39m\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 33m\Omega @ V_{GS}=10V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- Battery switch
- DC/DC converter



SOT-89



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM8N03	VSM8N03-S9	SOT-89	Ø180mm	12mm	1000units

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	8	A
Drain Current-Pulsed (Note 1)	I_{DM}	30	A
Maximum Power Dissipation	P_D	3.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	35	$^{\circ}C/W$
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Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA

Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.7	0.9	1.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =4A	-	33	55	mΩ
		V _{GS} =4.5V, I _D =5A	-	26	39	mΩ
		V _{GS} =10V, I _D =8A	-	24	33	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =8A	10	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	595	-	PF
Output Capacitance	C _{OSS}		-	39	-	PF
Reverse Transfer Capacitance	C _{rSS}		-	36	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, R _L =1.8Ω V _{GS} =10V,R _{GEN} =3Ω	-	3.0	-	nS
Turn-on Rise Time	t _r		-	4.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	25	-	nS
Turn-Off Fall Time	t _f		-	3.8	-	nS
Total Gate Charge	Q _g	V _{DS} =15V,I _D =8A, V _{GS} =4.5V	-	9.3	-	nC
Gate-Source Charge	Q _{gs}		-	1.6	-	nC
Gate-Drain Charge	Q _{gd}		-	2.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =8A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	8	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

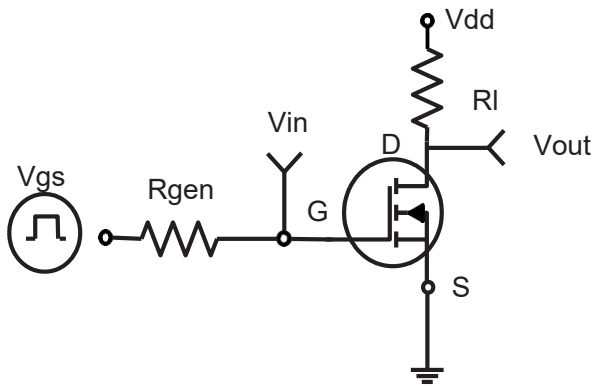


Figure 1: Switching Test Circuit

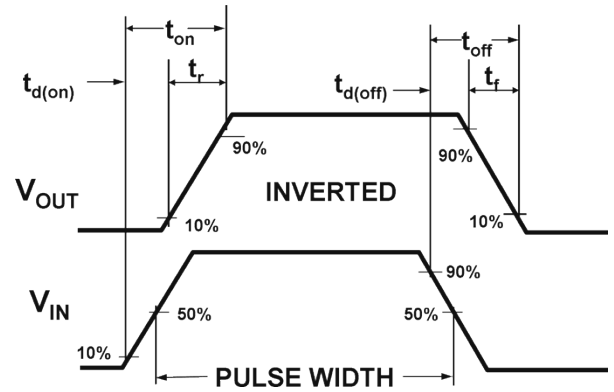


Figure 2: Switching Waveforms

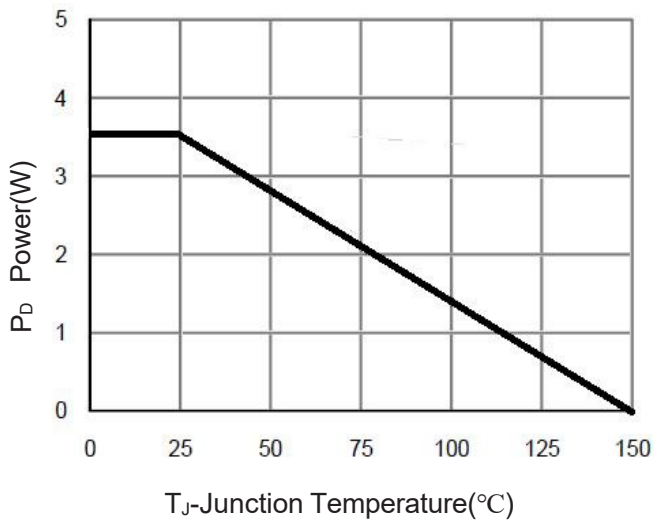


Figure 3 Power Dissipation

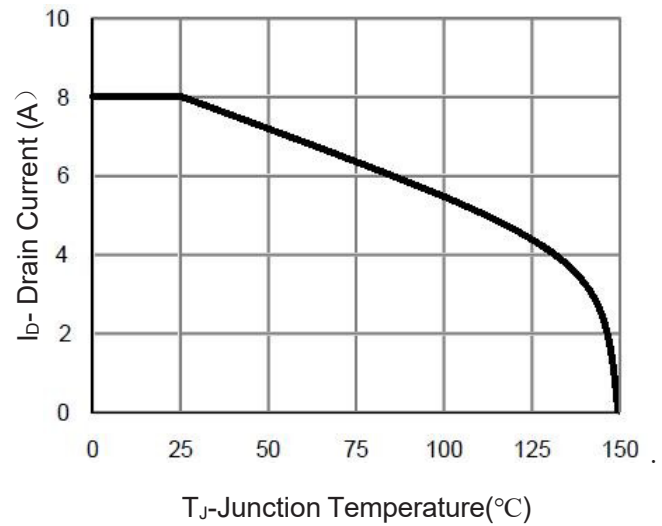


Figure 4 Drain Current

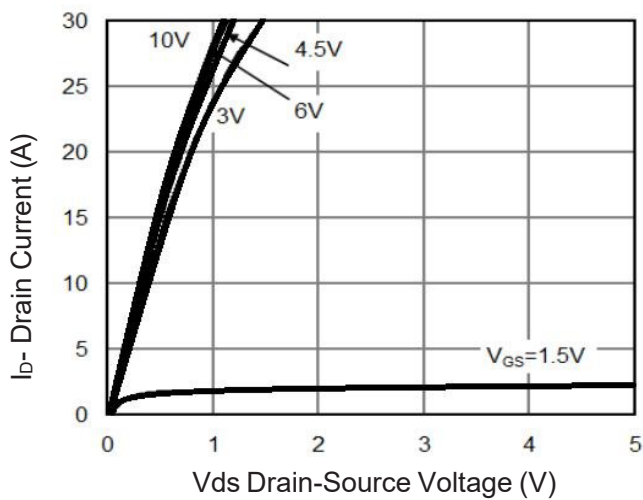


Figure 5 Output Characteristics

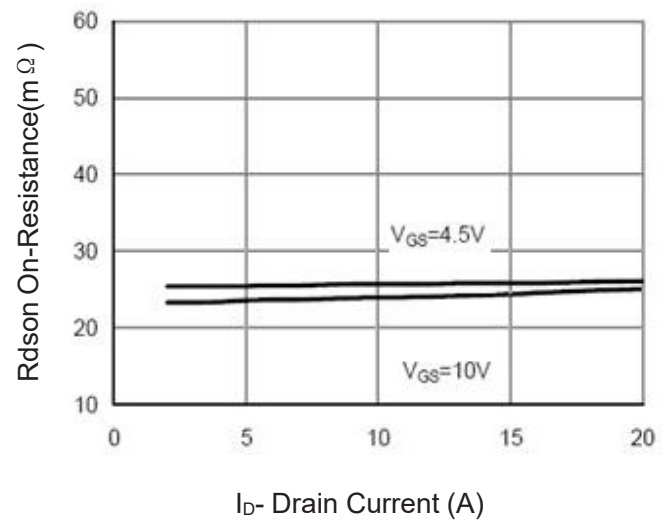
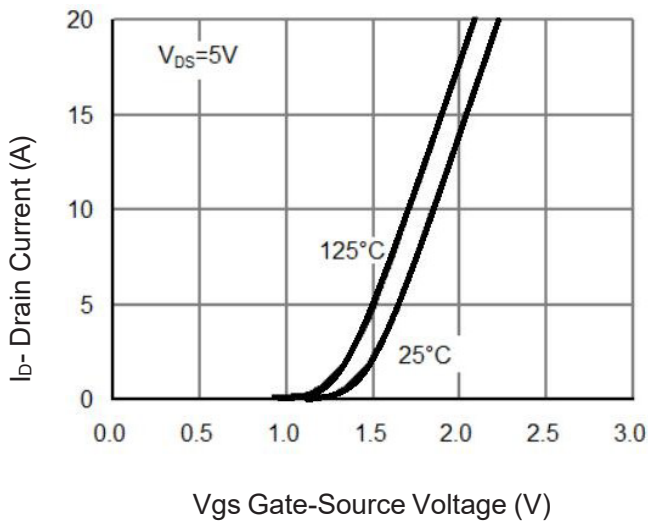
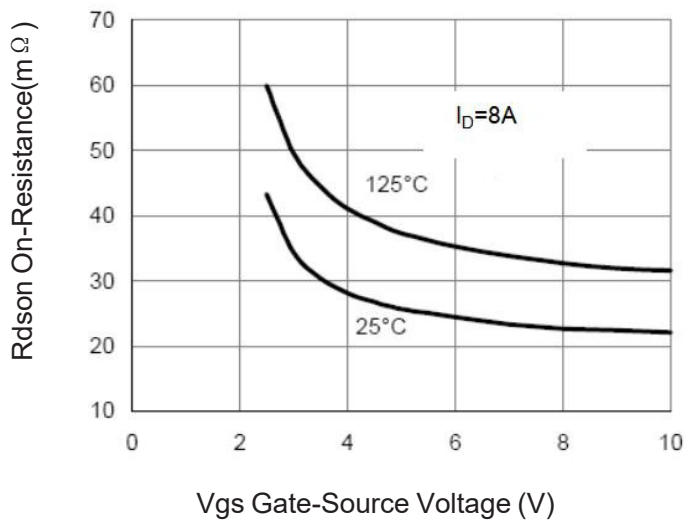
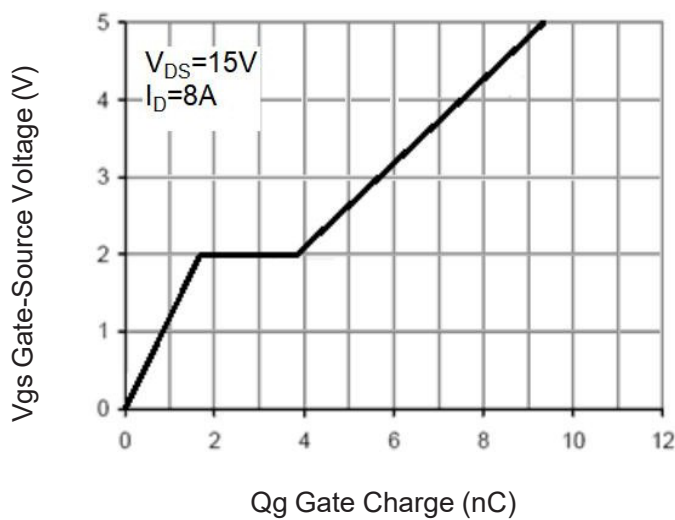
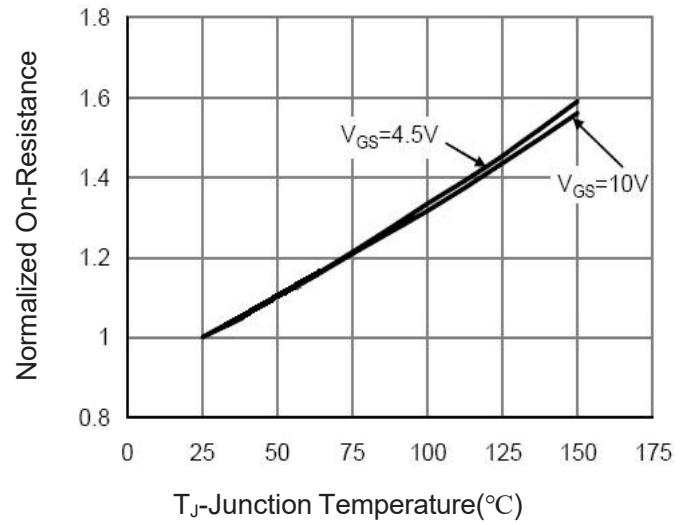
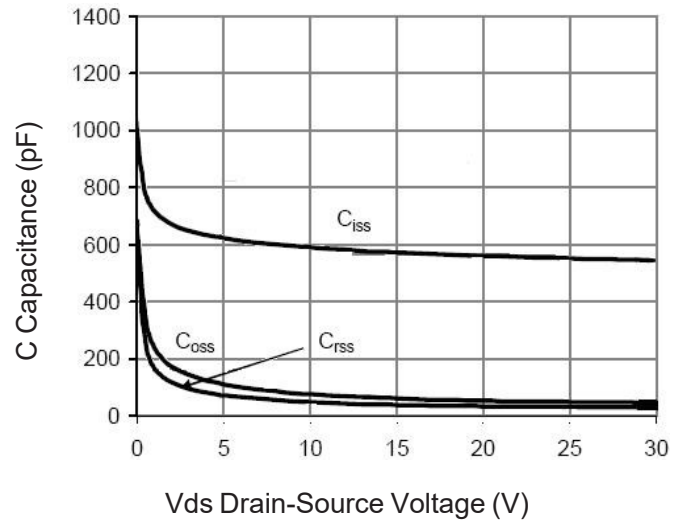
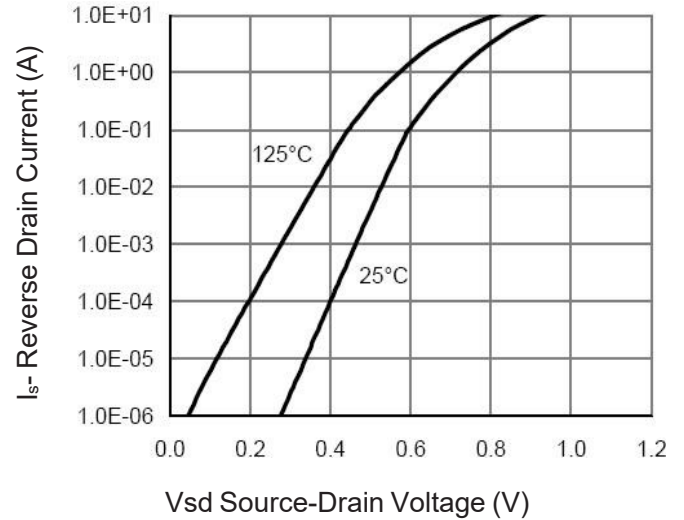
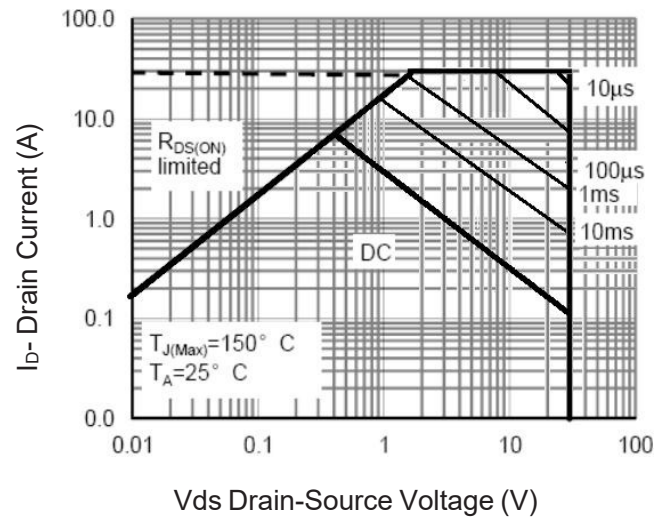
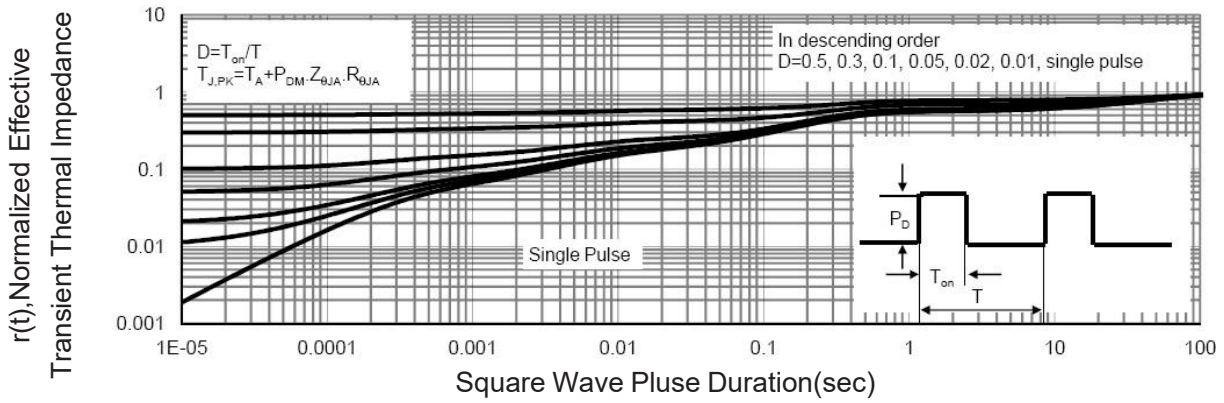


Figure 6 Drain-Source On-Resistance


Figure 7 Transfer Characteristics

Figure 9 Rdson vs Vgs

Figure 11 Gate Charge

Figure 8 Drain-Source On-Resistance

Figure 10 Capacitance vs Vds

Figure 12 Source- Drain Diode Forward


Figure 13 Safe Operation Area

Figure 14 Normalized Maximum Transient Thermal Impedanc